


“Low Side Chopper” IGBT SOT-227 (Warp 2 Speed IGBT), 70 A



SOT-227

PRIMARY CHARACTERISTICS	
V_{CES}	600 V
I_C DC	70 A at 87 °C
$V_{CE(on)}$ typical at 70 A, 25 °C	2.31 V
I_F DC	70 A at 86 °C
Package	SOT-227
Circuit configuration	Low side chopper

FEATURES

- NPT warp 2 speed IGBT technology with positive temperature coefficient
- Higher switching frequency up to 150 kHz
- Square RBSOA
- Low $V_{CE(on)}$
- FRED Pt[®] hyperfast rectifier
- Fully isolated package
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting to heatsink
- Plug-in compatible with other SOT-227 packages
- Lower conduction losses and switching losses
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C	$T_C = 25\text{ °C}$	109	A
		$T_C = 80\text{ °C}$	75	
Pulsed collector current	I_{CM}		120	
Clamped inductive load current	I_{LM}		120	
Diode continuous forward current	I_F	$T_C = 25\text{ °C}$	113	
		$T_C = 80\text{ °C}$	75	
Single pulse forward current	I_{FSM}	10 ms sine or 6 ms rectangular pulse, $T_J = 25\text{ °C}$	390	
Gate to emitter voltage	V_{GE}		± 20	
Power dissipation, IGBT	P_D	$T_C = 25\text{ °C}$	447	W
		$T_C = 80\text{ °C}$	250	
Power dissipation, diode	P_D	$T_C = 25\text{ °C}$	236	
		$T_C = 80\text{ °C}$	132	
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	V



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 35\text{ A}$	-	1.73	2.0	
		$V_{GE} = 15\text{ V}, I_C = 70\text{ A}$	-	2.31	-	
		$V_{GE} = 15\text{ V}, I_C = 35\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	2.14	-	
		$V_{GE} = 15\text{ V}, I_C = 70\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	3.0	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 500\text{ }\mu\text{A}$	2.7	4.5	5.4	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$ ($25\text{ }^\circ\text{C}$ to $125\text{ }^\circ\text{C}$)	-	-10.8	-	mV/ $^\circ\text{C}$
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$	-	5	50	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	0.17	-	mA
Diode reverse breakdown voltage	V_{BR}	$I_R = 1\text{ mA}$	600	-	-	V
Diode forward voltage drop	V_{FM}	$I_F = 35\text{ A}, V_{GE} = 0\text{ V}$	-	1.67	2.33	V
		$I_F = 70\text{ A}, V_{GE} = 0\text{ V}$	-	1.96	-	
		$I_F = 35\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	1.23	-	
		$I_F = 70\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	1.55	-	
Diode reverse leakage current	I_{RM}	$V_R = 600\text{ V}$	-	0.1	50	μA
		$T_J = 125\text{ }^\circ\text{C}, V_R = 600\text{ V}$	-	0.04	-	mA
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 200	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q_g	$I_C = 50\text{ A}, V_{CC} = 400\text{ V}, V_{GE} = 15\text{ V}$	-	320	-	nC	
Gate to emitter charge (turn-on)	Q_{ge}		-	42	-		
Gate to collector charge (turn-on)	Q_{gc}		-	110	-		
Turn-on switching loss	E_{on}	$I_C = 70\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = 15\text{ V}, R_g = 4.7\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$ Energy losses include tail and diode recovery	-	0.33	-	mJ	
Turn-off switching loss	E_{off}		-	0.46	-		
Total switching loss	E_{tot}		-	0.79	-		
Turn-on switching loss	E_{on}		-	0.51	-		
Turn-off switching loss	E_{off}		-	0.56	-		
Total switching loss	E_{tot}		-	1.07	-		
Turn-on delay time	$t_{d(on)}$		$I_C = 70\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = 15\text{ V}, R_g = 4.7\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$	-	166	-	ns
Rise time	t_r			-	44	-	
Turn-off delay time	$t_{d(off)}$			-	188	-	
Fall time	t_f			-	53	-	
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 120\text{ A}, R_g = 22\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 400\text{ V}, V_P = 600\text{ V}$	Fullsquare				
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, di/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}$	-	64	-	ns	
Diode peak reverse current	I_{rr}		-	4.5	-	A	
Diode recovery charge	Q_{rr}		-	144	-	nC	
Diode reverse recovery time	t_{rr}	$I_F = 50\text{ A}, di/dt = 200\text{ A}/\mu\text{s}, V_R = 200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	136	-	ns	
Diode peak reverse current	I_{rr}		-	12	-	A	
Diode recovery charge	Q_{rr}		-	807	-	nC	



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T_J, T_{Stg}		-40	-	150	°C
Junction to case	IGBT		-	-	0.28	°C/W
	Diode		-	-	0.53	
Case to heatsink	R_{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style		SOT-227				

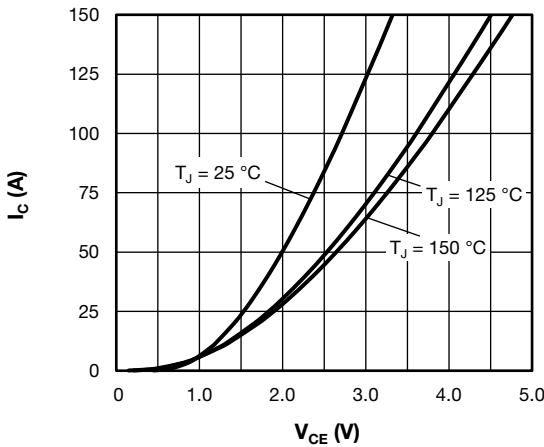


Fig. 1 - Typical IGBT Output Characteristics, $V_{GE} = 15\text{ V}$

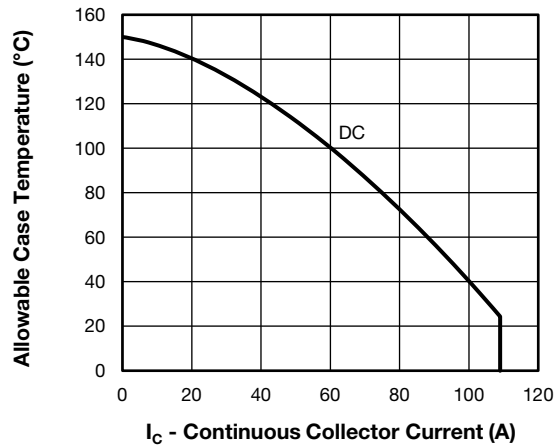


Fig. 3 - Maximum IGBT Continuous Collector Current vs. Case Temperature

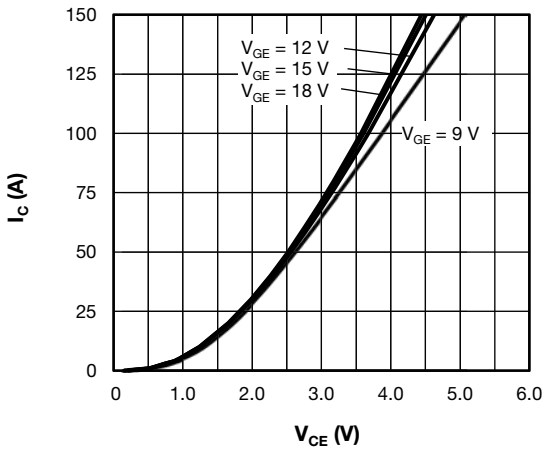


Fig. 2 - Typical IGBT Output Characteristics, $T_J = 125\text{ °C}$

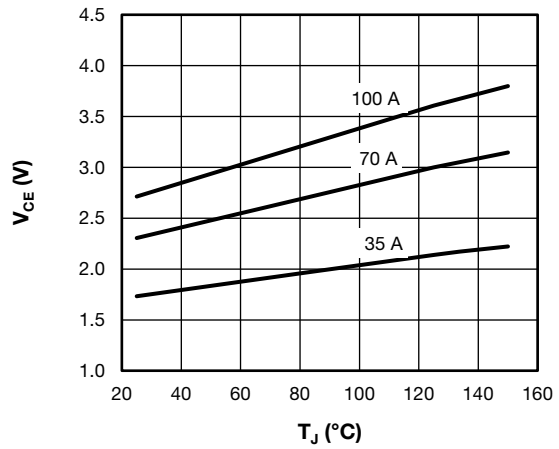


Fig. 4 - Collector to Emitter Voltage vs. Junction Temperature

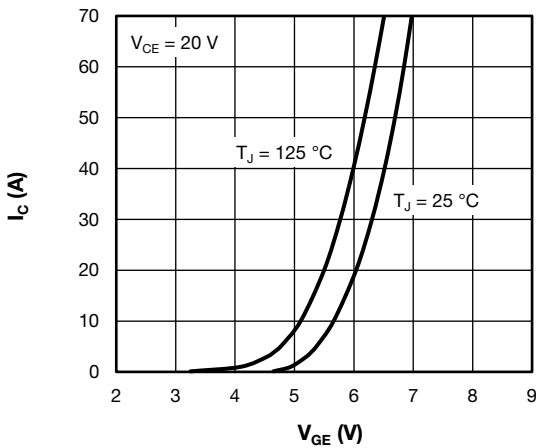


Fig. 5 - Typical IGBT Transfer Characteristics

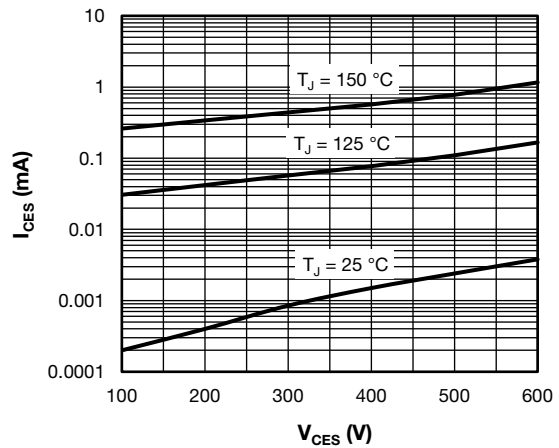


Fig. 8 - Typical IGBT Zero Gate Voltage Collector Current

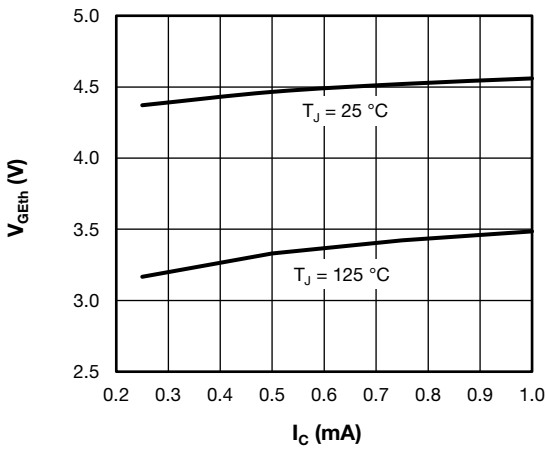


Fig. 6 - Typical IGBT Gate Threshold Voltage

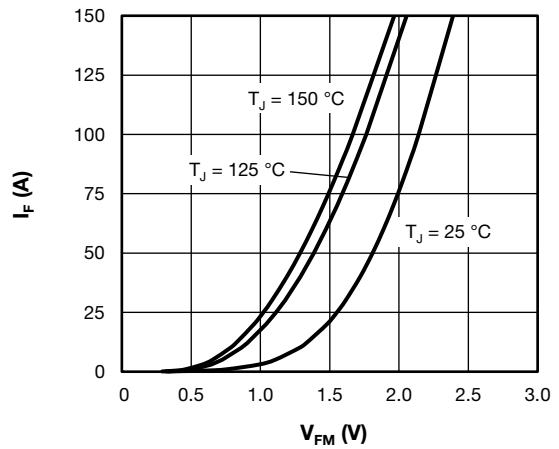


Fig. 9 - Typical Diode Forward Characteristics

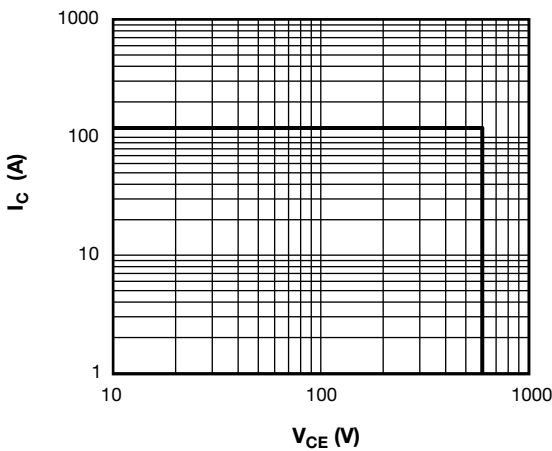


Fig. 7 - IGBT Reverse BIAS SOA,
 $T_J = 150\text{ }^\circ\text{C}$, $V_{GE} = 15\text{ V}$

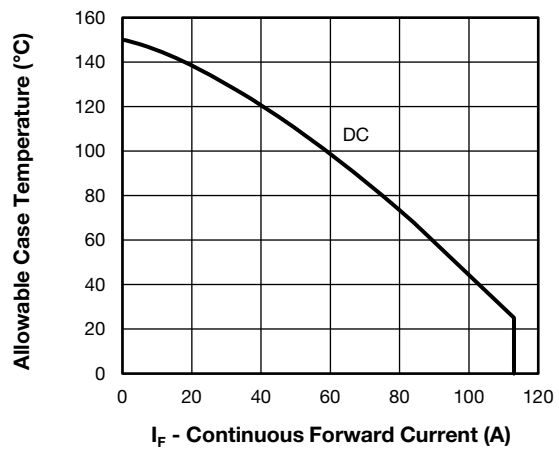


Fig. 10 - Maximum Diode Continuous Forward Current vs. Case Temperature

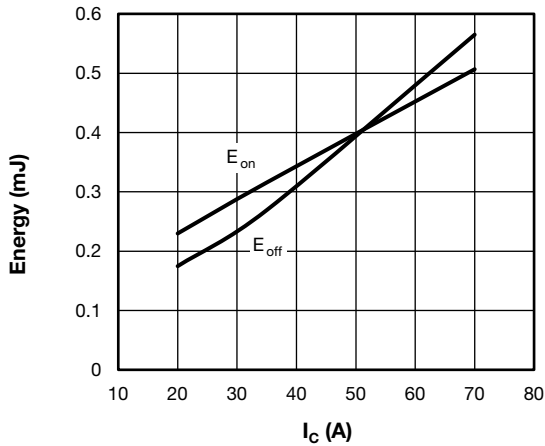


Fig. 11 - Typical IGBT Energy Loss vs. I_C
 $T_J = 125\text{ }^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

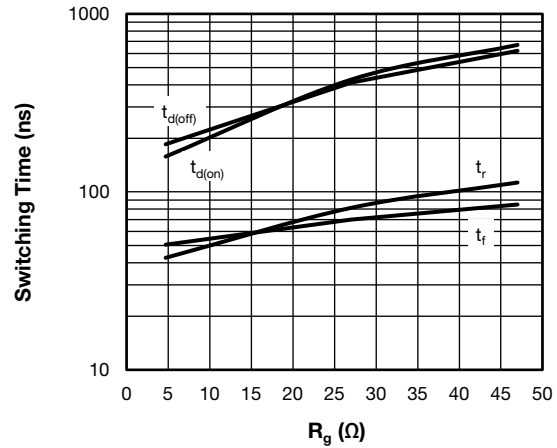


Fig. 14 - Typical IGBT Switching Time vs. R_g
 $T_J = 125\text{ }^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 70\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

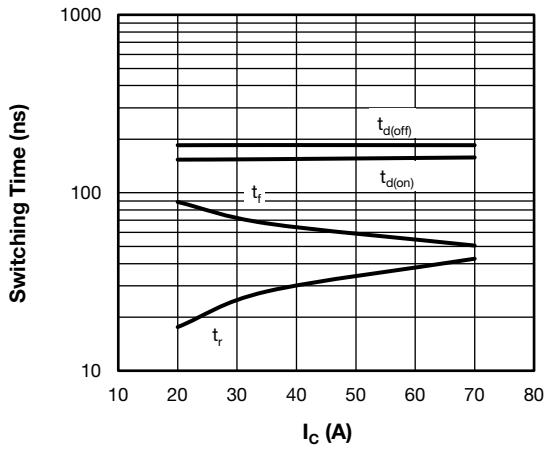


Fig. 12 - Typical IGBT Switching Time vs. I_C
 $T_J = 125\text{ }^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

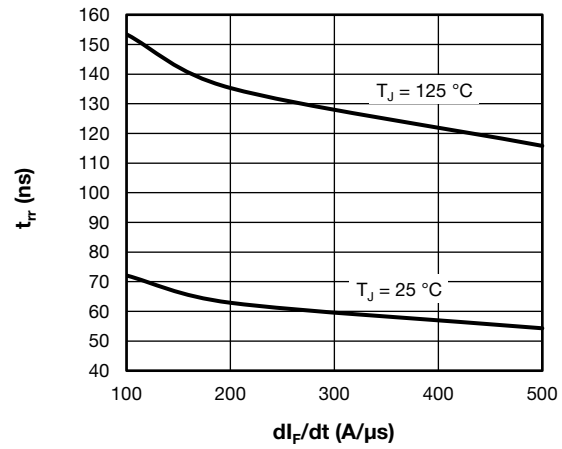


Fig. 15 - Typical Diode Reverse Recovery Time vs. di_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

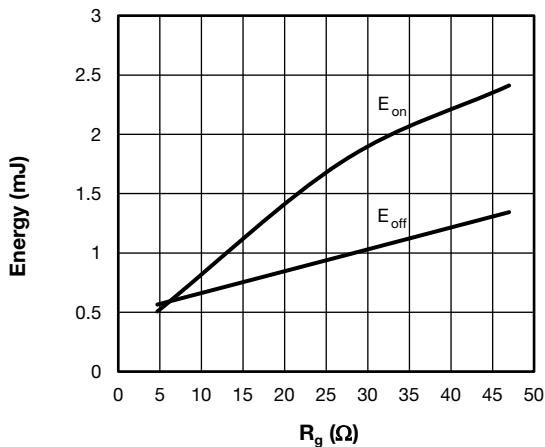


Fig. 13 - Typical IGBT Energy Loss vs. R_g
 $T_J = 125\text{ }^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 70\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

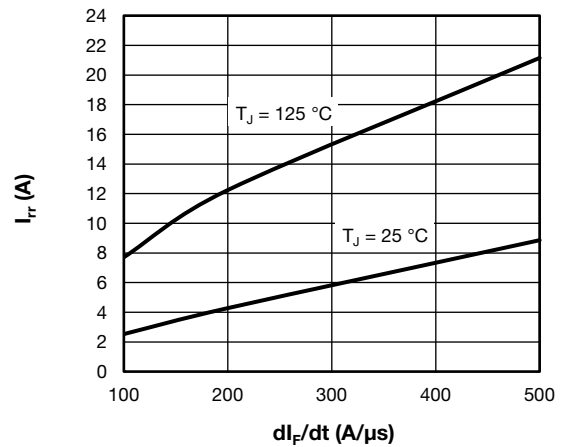


Fig. 16 - Typical Diode Reverse Recovery Current vs. di_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

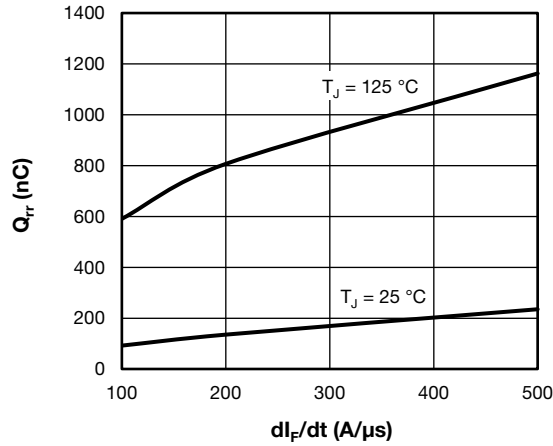


Fig. 17 - Typical Diode Reverse Recovery Charge vs. di_F/dt
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

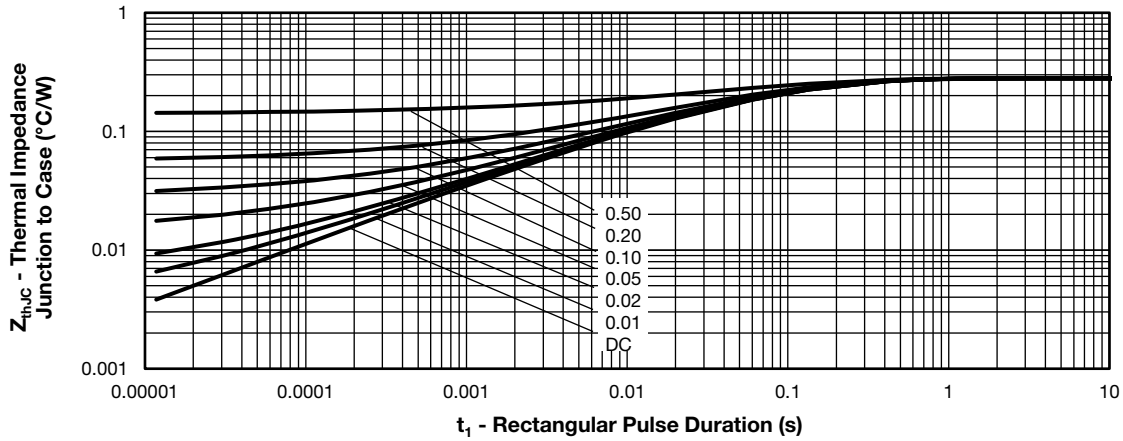


Fig. 18 - Maximum Thermal Impedance Z_{thJC} Characteristics (IGBT)

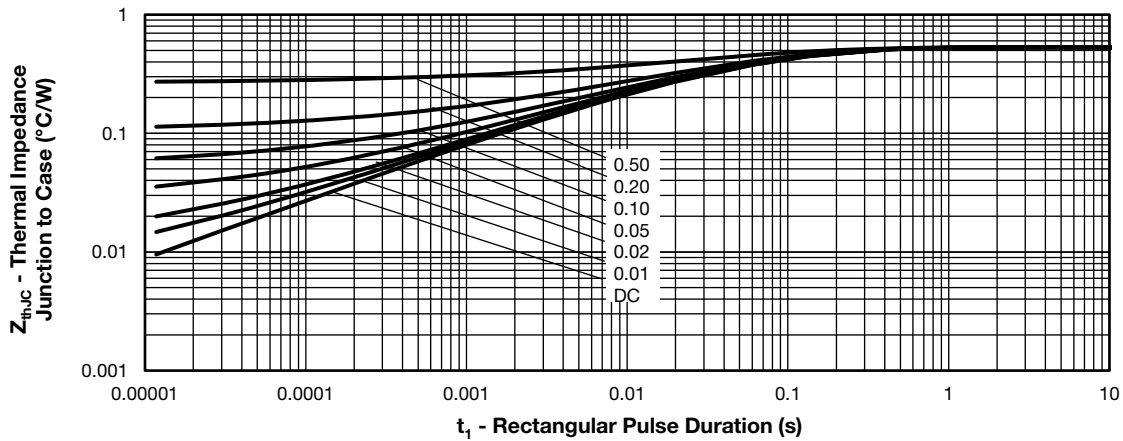


Fig. 19 - Maximum Thermal Impedance Z_{thJC} Characteristics (Diode)

ORDERING INFORMATION TABLE

Device code	VS-	G	B	75	L	A	60	U	F
	1	2	3	4	5	6	7	8	9

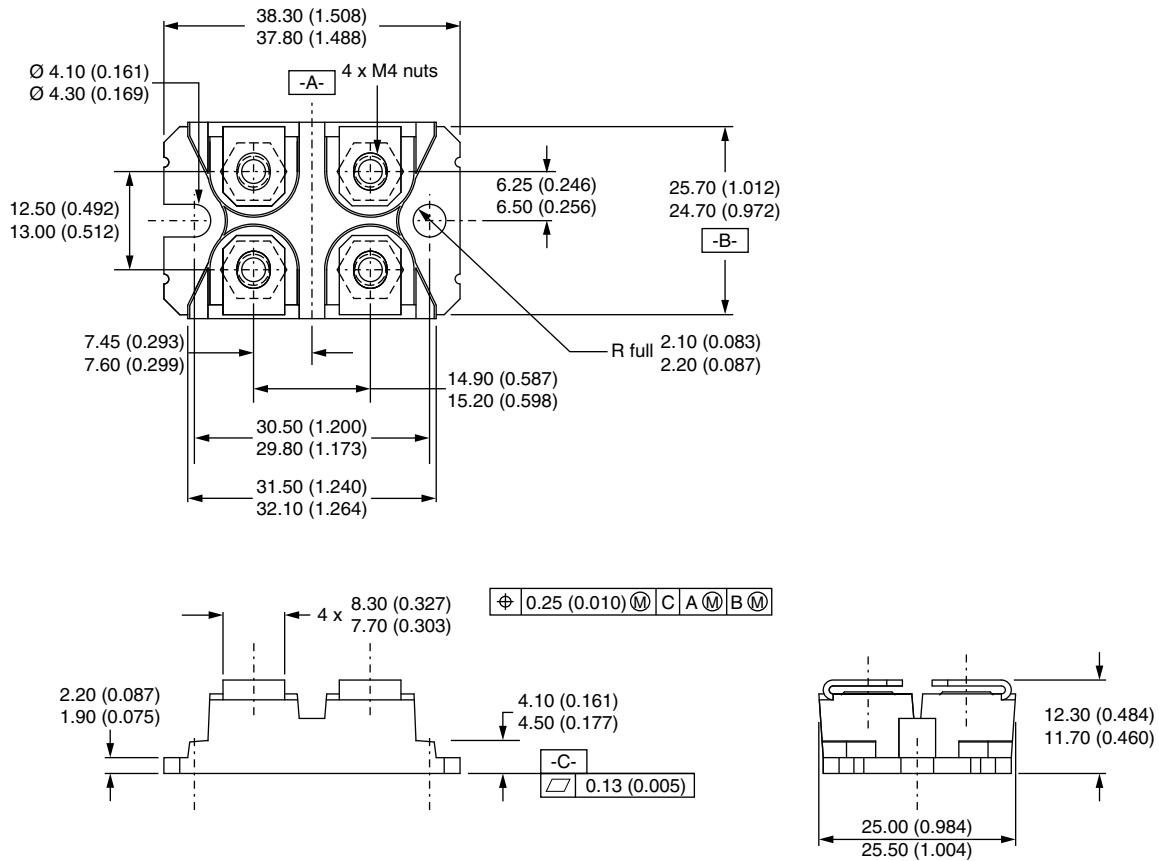
- 1** - Vishay Semiconductors product
- 2** - Insulated gate bipolar transistor (IGBT)
- 3** - B = IGBT Gen 5
- 4** - Current rating (75 = 70 A)
- 5** - Circuit configuration (L = low side chopper)
- 6** - Package indicator (A = SOT-227)
- 7** - Voltage rating (60 = 600 V)
- 8** - Speed/type (U = ultrafast IGBT)
- 9** - Diode (F = FRED Pt[®] diode)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Low side chopper	L	<p>Lead Assignment</p>

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Packaging information	www.vishay.com/doc?95425



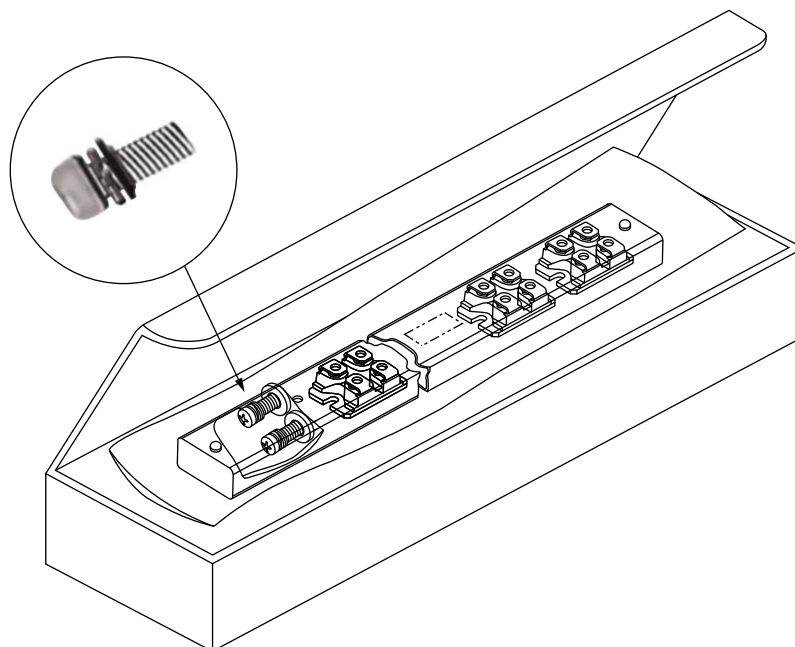
DIMENSIONS in millimeters (inches)



Note

- Controlling dimension: millimeter

PACKAGING INFORMATION





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